

atrin **electronic**

Expertise, variety and quality



www.atrinelec.com

آترین الکترونیک

تخصص، تنوع و کیفیت

02166766957 - 02166766927



info@atrinelec.com



تهران پاساژ امجد طبقه 1 واحد 16



@atrinelec



74HC05

Hex inverter with open-drain outputs

Rev. 02 — 18 June 2009

Product data sheet

1. General description

The 74HC05 is a high-speed Si-gate CMOS device that complies with JEDEC standard no. 7A.

The 74HC05 contains six inverters. The outputs of the 74HC05 are open-drain and can be connected to other open-drain outputs to implement active-LOW wired-OR or active-HIGH wired-AND functions. The open-drain outputs require pull-up resistors to perform correctly.

2. Features

- Wide operating voltage 2.0 V to 6.0 V
- Input levels:
 - ◆ For 74HC05: CMOS level
- Latch-up performance exceeds 100 mA per JESD 78 Class II level A
- ESD protection:
 - ◆ HBM JESD22-A114E exceeds 2000 V
 - ◆ CDM JESD22-C101C exceeds 1000 V
- Multiple package options
- Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC05D	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1
74HC05PW	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	TSSOP14	plastic thin shrink small outline package; 14 leads; body width 4.4 mm	SOT402-1
74HC05BQ	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	DHVQFN14	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body $2.5 \times 3 \times 0.85$ mm	SOT762-1

4. Functional diagram

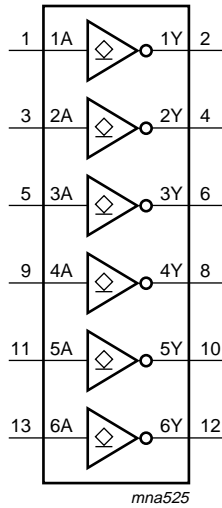


Fig 1. Logic symbol

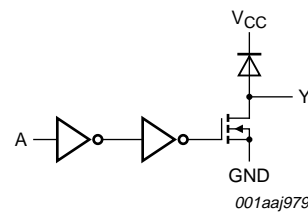


Fig 2. Logic diagram (one gate)

5. Pinning information

5.1 Pinning

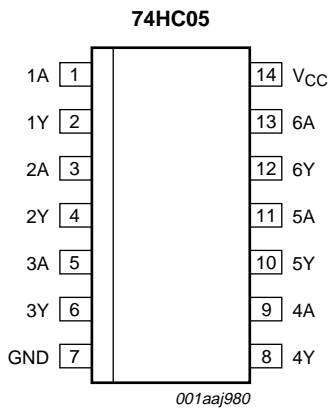
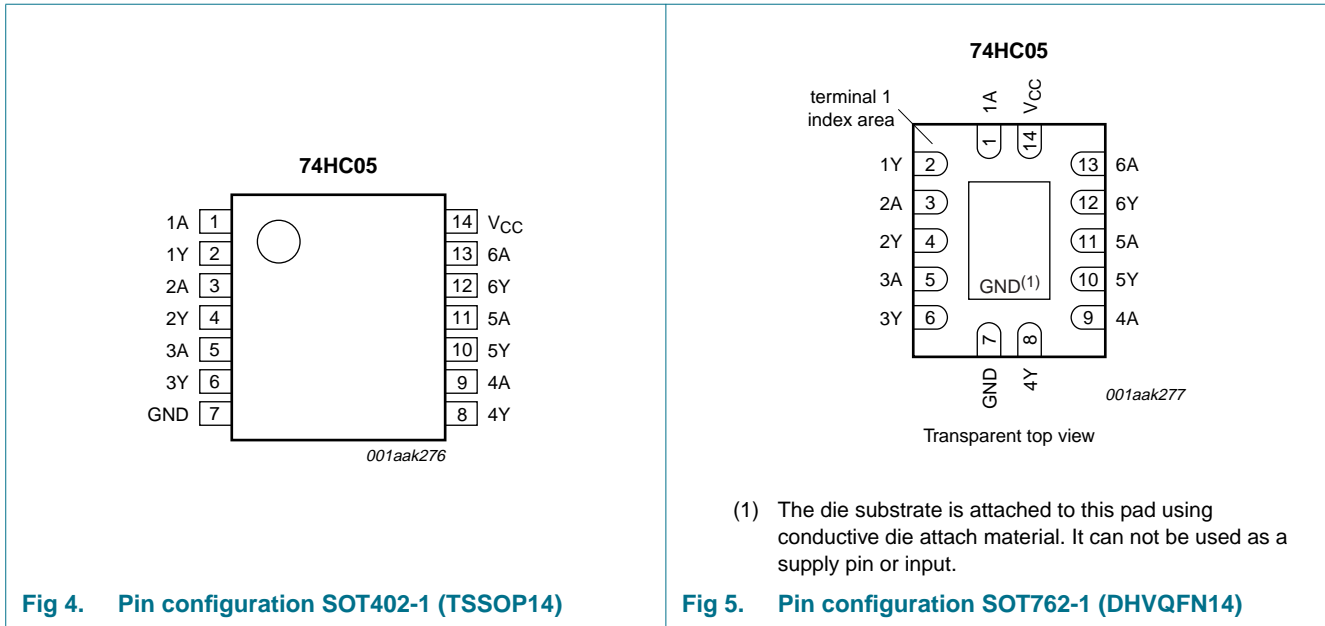


Fig 3. Pin configuration SOT108-1 (SO14)



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1A to 6A	1, 3, 5, 9, 11, 13	data input
1Y to 6Y	2, 4, 6, 8, 10, 12	data output
GND	7	ground (0 V)
V _{CC}	14	supply voltage

6. Functional description

Table 3. Function table^[1]

Input	Output
nA	nY
L	Z
H	L

[1] H = HIGH voltage level; L = LOW voltage level; Z = high-impedance OFF-state.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7	V
I _{IK}	input clamping current	V _I < -0.5 V or V _I > V _{CC} + 0.5 V	[1] -	20	mA
I _{OK}	output clamping current	V _O < -0.5 V or V _O > V _{CC} + 0.5 V	[1] -	20	mA
V _O	output voltage		[1] -0.5	V _{CC} + 0.5 V	V

Table 4. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
I_O	output current	$V_O < V_{CC} + 0.5\text{ V}$	-	25	mA
I_{CC}	supply current		-	50	mA
I_{GND}	ground current		-50	-	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation		[2] -	500	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

- [2] For SO14 package: P_{tot} derates linearly with 8 mW/K above 70 °C.
 For TSSOP14 packages: P_{tot} derates linearly with 5.5 mW/K above 60 °C.
 For DHVQFN14 packages: P_{tot} derates linearly with 4.5 mW/K above 60 °C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CC}	supply voltage		2.0	5.0	6.0	V
V_I	input voltage		0	-	V_{CC}	V
V_O	output voltage		0	-	V_{CC}	V
T_{amb}	ambient temperature		-40	-	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 2.0\text{ V}$	-	-	625	ns/V
		$V_{CC} = 4.5\text{ V}$	-	1.67	139	ns/V
		$V_{CC} = 6.0\text{ V}$	-	-	83	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
V_{IH}	HIGH-level input voltage	$V_{CC} = 2.0\text{ V}$	1.5	1.2	-	1.5	-	1.5	-	V
		$V_{CC} = 4.5\text{ V}$	3.15	2.4	-	3.15	-	3.15	-	V
		$V_{CC} = 6.0\text{ V}$	4.2	3.2	-	4.2	-	4.2	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 2.0\text{ V}$	-	0.8	0.5	-	0.5	-	0.5	V
		$V_{CC} = 4.5\text{ V}$	-	2.1	1.35	-	1.35	-	1.35	V
		$V_{CC} = 6.0\text{ V}$	-	2.8	1.8	-	1.8	-	1.8	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}								
		$I_O = 20\ \mu\text{A}; V_{CC} = 2.0\text{ V}$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20\ \mu\text{A}; V_{CC} = 4.5\text{ V}$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20\ \mu\text{A}; V_{CC} = 6.0\text{ V}$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 4.0\text{ mA}; V_{CC} = 4.5\text{ V}$	-	0.15	0.26	-	0.33	-	0.4	V
	$I_O = 5.2\text{ mA}; V_{CC} = 6.0\text{ V}$	-	0.16	0.26	-	0.33	-	0.4	V	

Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 6.0 V	-	-	0.1	-	1	-	1	µA
I _{OZ}	OFF-state output current	per input pin; V _I = V _{IL} ; V _O = V _{CC} or GND; other inputs at V _{CC} or GND; V _{CC} = 6.0 V; I _O = 0 A	-	-	0.5	-	5.0	-	10	µA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 6.0 V	-	-	2.0	-	20	-	40	µA
C _I	input capacitance		-	3.5	-	-	-	-	-	pF

10. Dynamic characteristics

Table 7. Dynamic characteristics

GND = 0 V; for test circuit see [Figure 7](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +125 °C		Unit
			Min	Typ	Max	Max (85 °C)	Max (125 °C)	
t _{PLZ}	LOW to OFF-state propagation delay	nA to nY; see Figure 6 V _{CC} = 2.0 V	-	20	90	115	135	ns
		V _{CC} = 4.5 V	-	11	18	23	27	ns
		V _{CC} = 6.0 V	-	10	15	20	23	ns
t _{PZL}	OFF-state to LOW propagation delay	nA to nY; see Figure 6 V _{CC} = 2.0 V	-	22	90	115	135	ns
		V _{CC} = 4.5 V	-	9	18	23	27	ns
		V _{CC} = 6.0 V	-	8	15	20	23	ns
t _{THL}	HIGH to LOW output transition time	see Figure 6 V _{CC} = 2.0 V	-	18	75	95	110	ns
		V _{CC} = 4.5 V	-	6	15	19	22	ns
		V _{CC} = 6.0 V	-	5	13	16	19	ns
C _{PD}	power dissipation capacitance	per inverter; V _I = GND to V _{CC} ; V _{CC} = 5.0 V	[1]	-	4	-	-	pF

[1] C_{PD} is used to determine the dynamic power dissipation (P_D in µW).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(0.5 \times C_L \times V_O^2 \times f_o) \text{ where:}$$

f_i = input frequency in MHz;

f_o = output frequency in MHz;

V_O = output voltage in V (output HIGH);

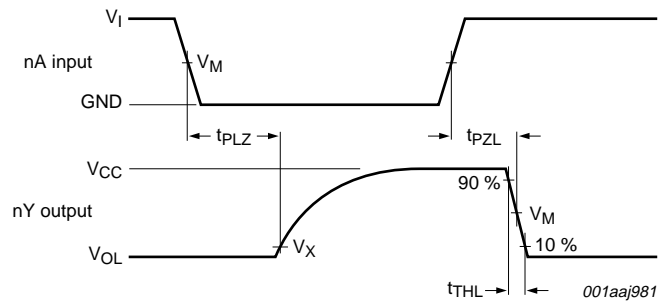
V_{CC} = supply voltage in V;

N = number of inputs switching;

R_L = load resistance in MΩ;

C_L = load capacitance in pF;

11. Waveforms



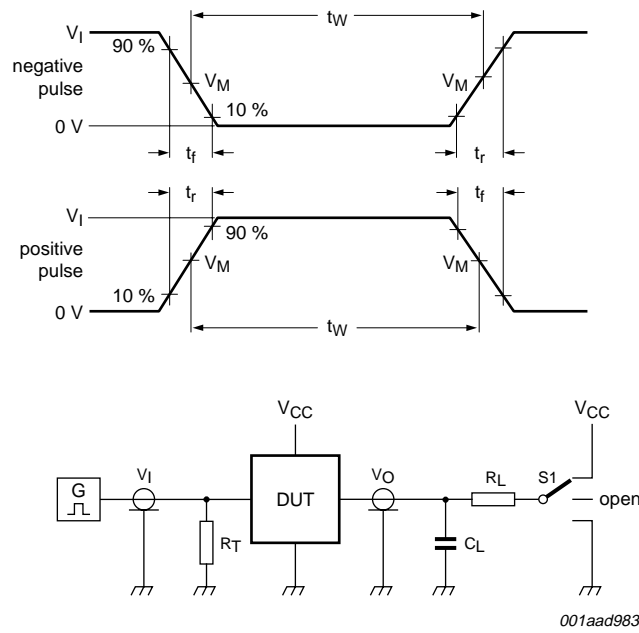
Measurement points are given in [Table 8](#).

V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 6. The input nA to output nY propagation delays and output transition times

Table 8. Measurement points

Input	Output	
V_M	V_M	V_X
$0.5V_{CC}$	$0.5V_{CC}$	$0.1V_{CC}$



Test data is given in [Table 9](#).

Definitions test circuit:

R_T = termination resistance should be equal to output impedance Z_o of the pulse generator.

C_L = load capacitance including jig and probe capacitance.

R_L = Load resistance.

Fig 7. Test circuit for measuring switching times

Table 9. Test data

Input		Load		S1 position
V_I	t_r, t_f	C_L	R_L	t_{PZL}, t_{PLZ}
V_{CC}	6 ns	50 pF	1 kΩ	V_{CC}

12. Package outline

SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1

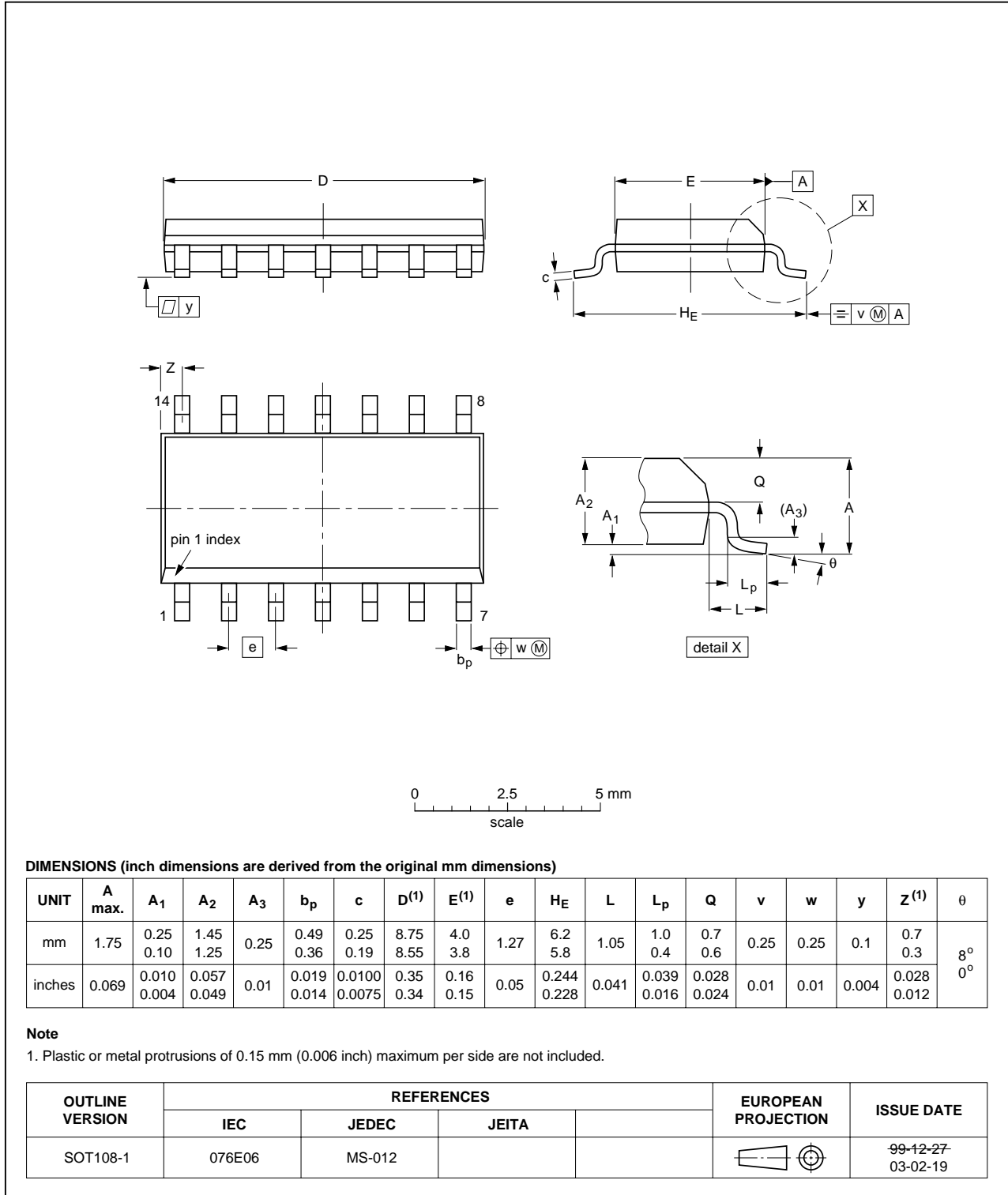


Fig 8. Package outline SOT108-1 (SO14)

TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1

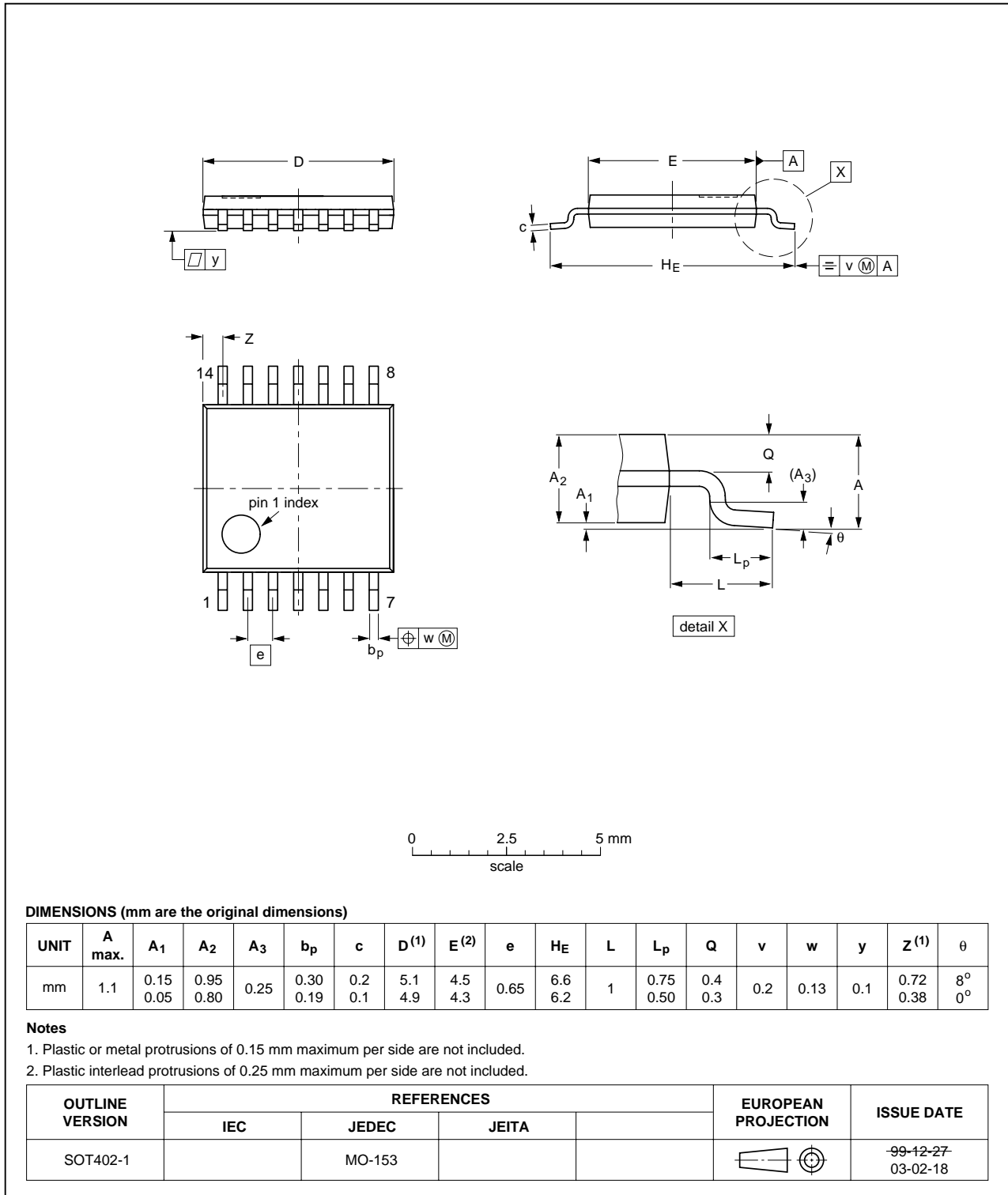


Fig 9. Package outline SOT402-1 (TSSOP14)

DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 x 3 x 0.85 mm

SOT762-1

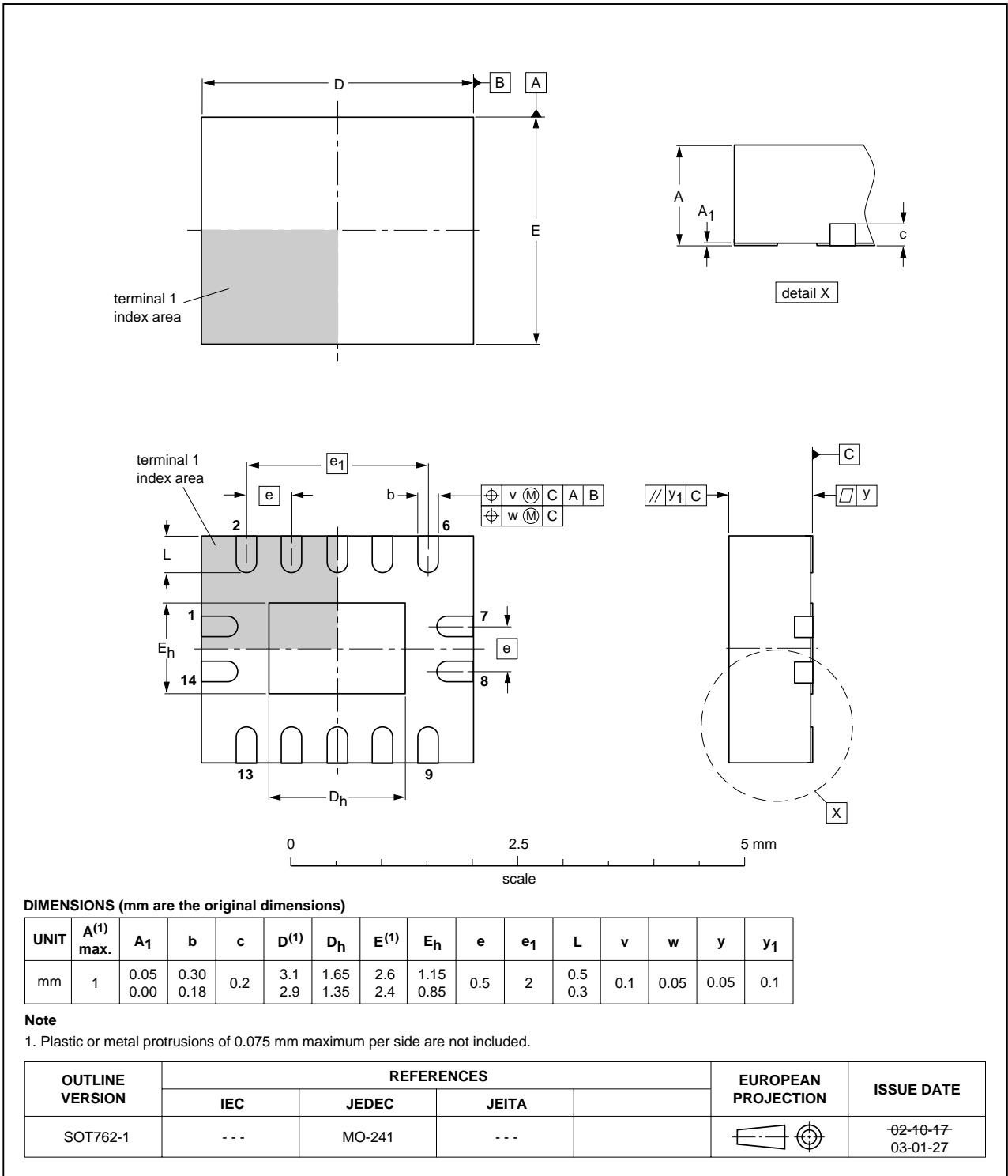


Fig 10. Package outline SOT762-1 (DHVQFN14)

13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC05_2	20090618	Product data sheet	-	74HC05_1
Modifications:	• Added type numbers 74HC05PW (TSSOP14 package) and 74HC05BQ (DHVQFN14 package)			
74HC05_1	20090427	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

15.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

15.3 Disclaimers

General — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental

damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

Terms and conditions of sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at <http://www.nxp.com/profile/terms>, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by NXP Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from national authorities.

15.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

16. Contact information

For more information, please visit: <http://www.nxp.com>

For sales office addresses, please send an email to: salesaddresses@nxp.com

17. Contents

1	General description	1
2	Features	1
3	Ordering information	1
4	Functional diagram	2
5	Pinning information	2
5.1	Pinning	2
5.2	Pin description	3
6	Functional description	3
7	Limiting values	3
8	Recommended operating conditions	4
9	Static characteristics	4
10	Dynamic characteristics	5
11	Waveforms	6
12	Package outline	8
13	Abbreviations	11
14	Revision history	11
15	Legal information	12
15.1	Data sheet status	12
15.2	Definitions	12
15.3	Disclaimers	12
15.4	Trademarks	12
16	Contact information	12
17	Contents	13

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.



© NXP B.V. 2009.

All rights reserved.

For more information, please visit: <http://www.nxp.com>

For sales office addresses, please send an email to: salesaddresses@nxp.com

Date of release: 18 June 2009

Document identifier: 74HC05_2